

IN THE CLAIMS:

1. (Previously Presented) A light-emitting device comprising:
  - a wiring formed on a first film;
  - a second film formed of the same layer as the wiring on the first film;
  - a third film formed over the first film;
  - a contact hole provided in the third film;
  - an electrode of a light-emitting element formed on the third film;
  - a fourth film covering an edge of the electrode of the light-emitting element,
    - wherein the electrode of the light-emitting element is formed so that at least a portion of the electrode of the light-emitting element is overlapped with the second film,
    - wherein the wiring is connected with the electrode of the light-emitting element in the contact hole,
    - wherein an opening of a the fourth film provided in an overlap portion of the electrode of the light-emitting element and the second film, and
    - wherein a contact hole of the third film is overlapped with the fourth film.
2. (Original) The light-emitting device according to claim 1, wherein a reflective film is included in the electrode of the light-emitting element.
3. (Original) The light-emitting device according to claim 1 or claim 2, wherein the wiring is integrated with the second film.
4. (Original) The light-emitting device according to claim 1, wherein the second film has a film thickness equal to or thicker than that of the wiring.
5. (Previously Presented) A light-emitting device comprising:
  - a transistor including a semiconductor film, a gate insulating film, and a gate electrode;

a first film formed on the transistor;  
a first contact hole provided in the first film;  
a wiring formed on the first film;  
a second film formed of the same layer as the wiring on the first film;  
a third film formed over the first film;  
a second contact hole provided in the third film;  
an electrode of a light-emitting element formed on the third film; and  
a fourth film covering an edge of the electrode of the light-emitting element,  
wherein the electrode of the light-emitting element is formed so that at  
least a portion of the electrode of the light-emitting element is overlapped with the  
second film,  
wherein an opening of a the fourth film is provided in an overlap  
portion of the electrode of the light-emitting element and the second film, and  
wherein a first contact hole of the first film and a second contact hole  
of the third film are overlapped with the fourth film.

6. (Original) The light-emitting device according to claim 5, wherein a reflective film  
is included in the electrode of the light-emitting element.

7. (Original) The light-emitting device according to claim 5 or claim 6, wherein the  
wiring is integrated with the second film.

8. (Original) The light-emitting device according to claim 5, wherein the second film  
has a film thickness equal to or thicker than that of the wiring.

9. (Previously Presented) A light-emitting device comprising:

a semiconductor film;  
a gate insulating film formed on the semiconductor film;  
a gate electrode formed on the gate insulating film;  
a first film formed on the gate electrode;  
a first contact hole provided in the first film;

a wiring formed on the first film;  
a second film formed of the same layer as the wiring on the first film;  
a third film formed over the first film; ~~and~~  
a second contact hole provided in the third film;  
an electrode of a light-emitting element formed on the third film~~[,]~~; and  
a fourth film covering an edge of the electrode of the light-emitting element,  
wherein the electrode of the light-emitting element is formed so that at  
least a portion of the electrode of the light-emitting element is overlapped with the  
second film,  
wherein an opening of the fourth film is provided in an overlap portion  
of the electrode of the light-emitting element and the second film, and  
wherein a first contact hole of the first film and a second contact hole  
of the third film are overlapped with the fourth film.

10. (Original) The light-emitting device according to claim 9, wherein a reflective film is provided in the electrode of the light-emitting element.

11. (Original) The light-emitting device according to claim 9 or claim 10, wherein the wiring is integrated with the second film.

12. (Original) The light-emitting device according to claim 9, wherein the second film has a film thickness equal to or thicker than that of the wiring.

13. (Previously Presented) A light-emitting device comprising:  
a conductive film formed on a first interlayer insulating film;  
a second interlayer insulating film formed over the first interlayer insulating film;  
an electrode of a light-emitting element formed on the second interlayer insulating film;

a contact hole provided in the second interlayer insulating film; and  
a partition layer covering an edge of the electrode of the light-emitting  
element,

wherein the electrode of the light-emitting element is electrically  
connected to the conductive film in the contact hole,

wherein the electrode of the light-emitting element is formed so that at  
least a portion of the electrode of the light-emitting element is overlapped with the  
conductive film,

wherein an opening of the partition layer is provided in an overlap  
portion of the electrode of the light-emitting element and the conductive film, and

wherein the contact hole of the second interlayer insulating film is  
overlapped with the partition layer.

14-17. (Canceled)

18. (Previously Presented) A light-emitting device comprising:

a conductive film formed over a first insulating film;  
a second insulating film formed over the first insulating film;  
an electrode of a light-emitting element formed over the second insulating  
film;

a contact hole provided in the second insulating film; and  
a partition layer covering an edge of the electrode of the light-emitting  
element,

wherein the electrode of the light-emitting element is electrically  
connected to the conductive film in the contact hole,

wherein the electrode of the light-emitting element is formed so that at  
least a portion of the electrode of the light-emitting element is overlapped with the  
conductive film,

wherein an opening of the partition layer is provided in an overlap portion of the electrode of the light-emitting element and the conductive film, and  
wherein the contact hole of the second insulating film is overlapped with the partition layer.

19. (Currently Amended) A light-emitting device comprising:  
a conductive film formed over a first insulating film;  
a second insulating film formed over the first insulating film;  
an electrode of a light-emitting element formed over the second insulating film;  
a partition layer covering an edge of the electrode of the light-emitting element; and  
a color filter formed over the electrode of the light-emitting element,  
wherein the electrode of the light-emitting element is electrically connected to the conductive film in ~~[[the]]~~ a contact hole,  
wherein the electrode of the light-emitting element is formed so that at least a portion of the electrode of the light-emitting element is overlapped with the conductive film,  
wherein an opening of the partition layer is provided in an overlap portion of the electrode of the light-emitting element and the conductive film, and  
wherein the color filter is overlapped with the overlap portion of the electrode of the light-emitting element and the conductive film.

20. (Previously Presented) The light-emitting device according to claim 1, wherein the light-emitting device is an active matrix display device.

21. (Previously Presented) The light-emitting device according to claim 13, wherein the light-emitting device is an active matrix display device.

22. (Previously Presented) The light-emitting device according to claim 18, wherein the light-emitting device is an active matrix display device.

23. (Previously Presented) The light-emitting device according to claim 19, wherein the light-emitting device is an active matrix display device.